



Sheet 1 of 1

Form 1449*

Atty. Docket No.: 303.691US1

Serial No. 09/584,566

INFORMATION DISCLOSURE STATEMENT
BY APPLICANT


Applicant: Leonard Forbes et al.

(Use several sheets if necessary)

Filing Date: May 31, 2000

Group: 2818

U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date
						If Appropriate
	5,386,132	01/01/1995	Wong	257	316	
	5,583,360	10/01/1996	Ruth, et al.	257	316	
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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No

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Sheet 1 of 2

Form 1449*	Atty. Docket No.: 303.691US1	Serial No. 09/584,566
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FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
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OTHER DOCUMENTS

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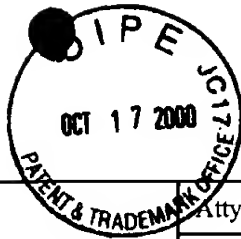
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